



ON Semiconductor®

FDS8433A

Single P-Channel 2.5V Specified MOSFET

General Description

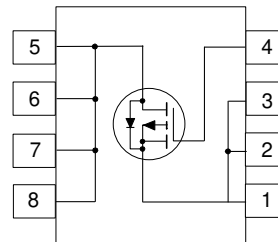
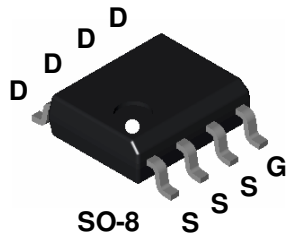
This P-Channel enhancement mode power field effect transistors is produced using ON Semiconductor's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance.

Applications

- Load switch
- DC/DC converter
- Battery protection

Features

- -5 A, -20 V. $R_{DS(on)} = 0.047 \Omega @ V_{GS} = -4.5 V$
 $R_{DS(on)} = 0.070 \Omega @ V_{GS} = -2.5 V$
- Fast switching speed.
- High density cell design for extremely low $R_{DS(on)}$.
- High power and current handling capability.



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

| Symbol | Parameter | FDS8433A | Units |
|-----------------------------------|--|-------------|-------|
| V _{DSS} | Drain-Source Voltage | -20 | V |
| V _{GSS} | Gate-Source Voltage | ±8 | V |
| I _D | Drain Current - Continuous (Note 1a) - Pulsed | -5 | A |
| | | -50 | |
| P _D | Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c) | 2.5 | W |
| | | 1.2 | |
| | | 1 | |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|------------------|---|----|------|
| R _{θJA} | Thermal Resistance, Junction-to-Ambient (Note 1a) | 50 | °C/W |
| R _{θJC} | Thermal Resistance, Junction-to-Case (Note 1) | 25 | °C/W |

Package Outlines and Ordering Information

| Device Marking | Device | Reel Size | Tape Width | Quantity |
|----------------|----------|-----------|------------|------------|
| FDS8433A | FDS8433A | 13" | 12mm | 2500 units |

DMOS Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|-----------------------------------|---|--|-----|-----|------|----------------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$ | -20 | | | V |
| $\frac{BV_{DSS}}{\Delta T_{j,l}}$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\ \mu\text{A}$, Referenced to 25°C | | -25 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$ | | | -1 | μA |
| I_{GSSF} | Gate-Body Leakage Current, Forward | $V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$ | | | 100 | nA |
| I_{GSSR} | Gate-Body Leakage Current, Reverse | $V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$ | | | -100 | nA |

On Characteristics (Note 2)

| | | | | | | |
|--|--|--|------|-------------------------|-------------------------|----------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$ | -0.4 | -0.6 | -1 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_{j,l}}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = -250\ \mu\text{A}$, Referenced to 25°C | | 4 | | mV/ $^\circ\text{C}$ |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = -2.5\text{ V}, I_D = -4.3\text{ A}$ | | 0.036 0.050 0.047 | 0.047 0.085 0.070 | Ω |
| $I_{D(on)}$ | On-State Drain Current | $V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$ | -25 | | | A |
| g_{FS} | Forward Transconductance | $V_{DS} = -5\text{ V}, I_D = -5\text{ A}$ | | 16 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|---|--|------|--|----|
| C_{iss} | Input Capacitance | $V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$ | | 1130 | | pF |
| C_{oss} | Output Capacitance | | | 480 | | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 120 | | pF |

Switching Characteristics (Note 2)

| | | | | | | |
|--------------|---------------------|--|--|-----|-----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$ | | 8 | 16 | ns |
| t_r | Turn-On Rise Time | | | 23 | 37 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 260 | 360 | ns |
| t_f | Turn-Off Fall Time | | | 90 | 125 | ns |
| Q_g | Total Gate Charge | $V_{DS} = -5\text{ V}, I_D = -5\text{ A},$ $V_{GS} = -5\text{ V},$ | | 20 | 28 | nC |
| Q_{gs} | Gate-Source Charge | | | 2.8 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 3.2 | | nC |

Drain-Source Diode Characteristics and Maximum Ratings

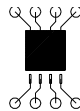
| | | | | | | |
|----------|---|---|--|------|------|---|
| I_S | Maximum Continuous Drain-Source Diode Forward Current | | | -2.1 | | A |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = -2.1\text{ A}$ (Note 2) | | -0.8 | -1.2 | V |

Notes:

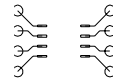
1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1 in^2 pad of 2 oz. copper.



b) 105°C/W when mounted on a 0.04 in^2 pad of 2 oz. copper.



c) 125°C/W on a minimum mounting pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

2: Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

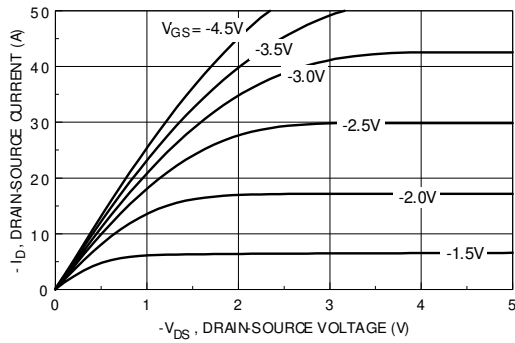


Figure 1. On-Region Characteristics.

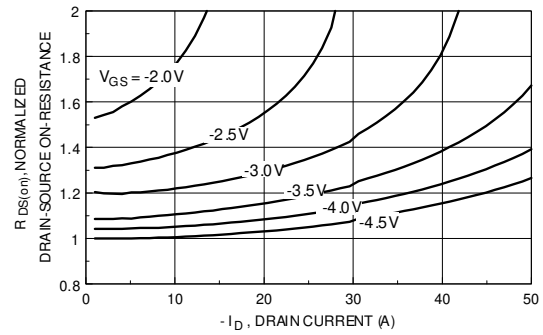


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

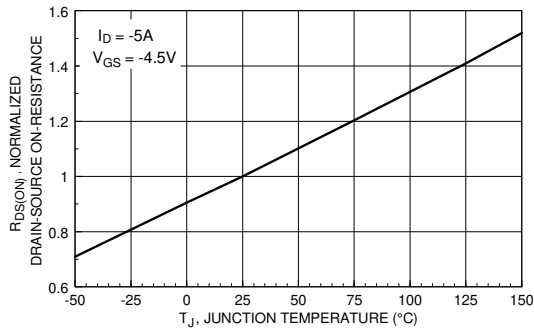


Figure 3. On-Resistance Variation with Temperature.

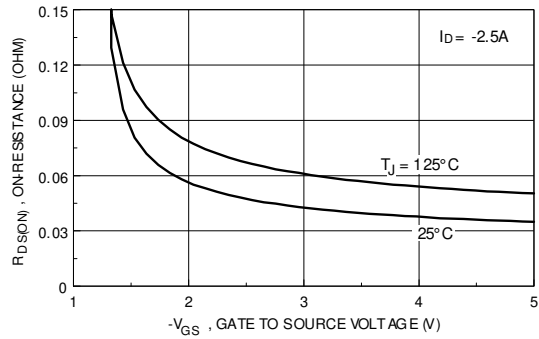


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

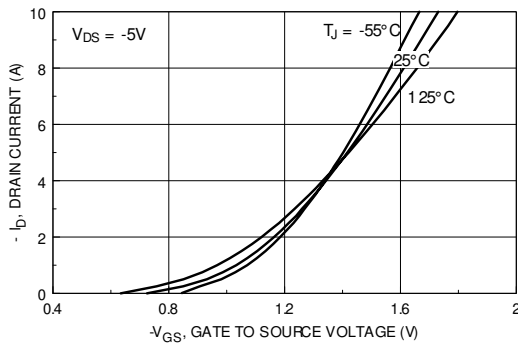


Figure 5. Transfer Characteristics.

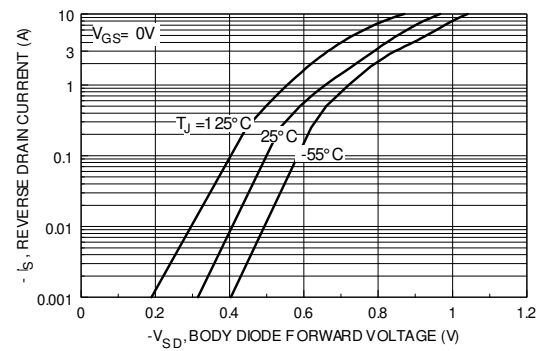


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

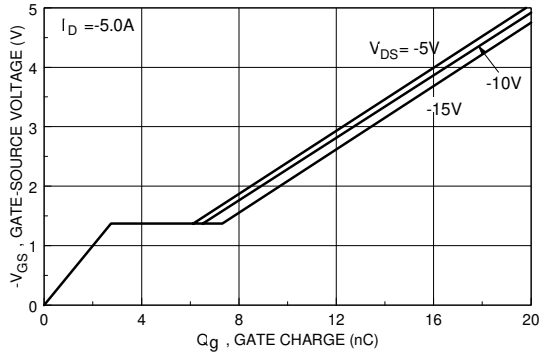


Figure 7. Gate-Charge Characteristics.

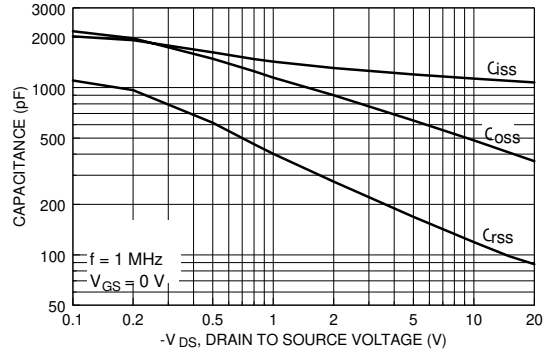


Figure 8. Capacitance Characteristics.

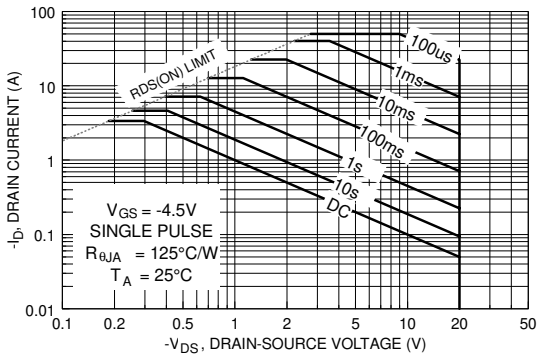


Figure 9. Maximum Safe Operating Area.

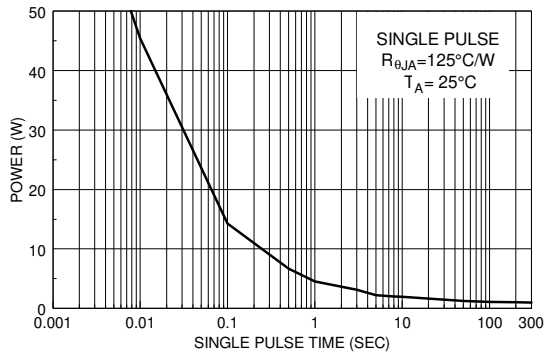


Figure 10. Single Pulse Maximum Power Dissipation.

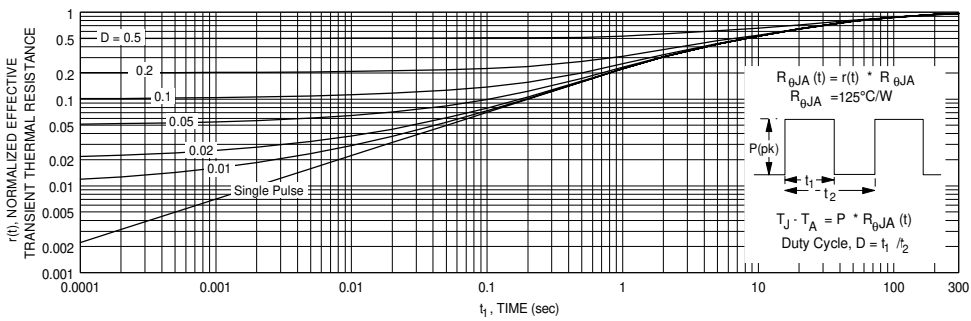



Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.

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